# **MA3X717** (MA717)

### Silicon epitaxial planar type

For switching

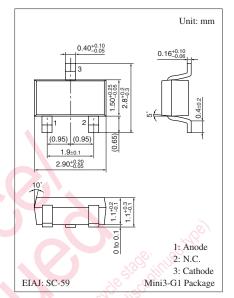
For wave detection

#### Features

- $\bullet$  Low forward voltage  $V_{\rm F}$  , optimum for low voltage rectification
- Low V<sub>F</sub> type of MA3X704A (MA704A)
- Optimum for high frequency rectification because of its short reverse recovery time t<sub>rr</sub>

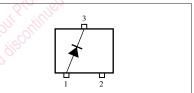
| Ŭ                            |                  |             |      |  |  |  |  |
|------------------------------|------------------|-------------|------|--|--|--|--|
| Parameter                    | Symbol           | Rating      | Unit |  |  |  |  |
| Reverse voltage              | V <sub>R</sub>   | 30          | V    |  |  |  |  |
| Maximum peak reverse voltage | V <sub>RM</sub>  | 30          | V    |  |  |  |  |
| Peak forward current         | I <sub>FM</sub>  | 150         | mA   |  |  |  |  |
| Forward current              | $I_{\rm F}$      | 30          | mA   |  |  |  |  |
| Junction temperature         | Tj               | 125         | °Ċ   |  |  |  |  |
| Storage temperature          | T <sub>stg</sub> | -55 to +125 | °C   |  |  |  |  |
|                              |                  |             |      |  |  |  |  |

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$



#### Marking Symbol: M2M

#### Internal Connection

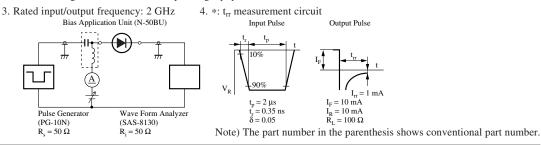


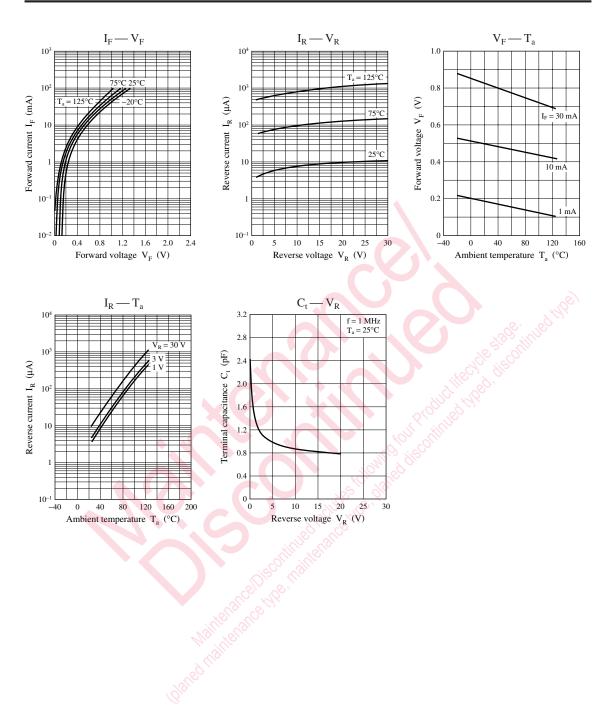
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter               | Symbol          | Conditions                                       | Min | Тур | Max | Unit |
|-------------------------|-----------------|--|-----|-----|-----|------|
| Forward voltage         | V <sub>F1</sub> | $I_F = 1 \text{ mA}$                             |     |     | 0.3 | V    |
|                         | V <sub>F2</sub> | $I_F = 30 \text{ mA}$                            |     |     | 1.0 |      |
| Reverse current         | IR              | $V_R = 30 V$                                     |     |     | 30  | μΑ   |
| Terminal capacitance    | Ct              | $V_R = 1 V, f = 1 MHz$                           |     | 1.5 |     | pF   |
| Reverse recovery time * | t <sub>r</sub>  | $I_F = I_R = 10 \text{ mA}$                      |     | 1.0 |     | ns   |
|                         | Nghi Cho        | $I_{rr} = 1 \text{ mA}, R_L = 100 \Omega$        |     |     |     |      |
| Detection efficiency    | n               | $V_{IN} = 3 V_{(peak)}$ , f = 30 MHz             |     | 65  |     | %    |
|                         | 96.             | $R_L = 3.9 \text{ k}\Omega, C_L = 10 \text{ pF}$ |     |     |     |      |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.





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